

In the Claims:

Please amend claim 17 as indicated below. This listing of claims replaces all prior versions.

1. (previously presented) A method for chemical-mechanical polishing a wafer using a CMP apparatus having a polishing table including a polishing pad and a wafer carrier adapted to carry a wafer relative to the center of the polishing table, the method comprising:
 - using the polishing pad, polishing the wafer at a position relative to the center;
 - determining that the wafer is being polished in a center-offset manner; and
 - as a function of the wafer being polished in the center-offset manner, conditioning the pad and positioning the wafer carrier misaligned with respect to the pad.
2. (original) A method for chemical-mechanical polishing, according to claim 1, wherein the center-offset manner includes at least one of: a center-fast or center-slow manner, and further including inspecting a wafer during the polishing process.
3. (original) A method for chemical-mechanical polishing, according to claim 1, wherein determining that the wafer is being polished in a center-offset manner includes removing the wafer from the carrier and manually inspecting a wafer.
4. (original) A method for chemical-mechanical polishing, according to claim 1, wherein the wafer is being polished in a center-fast manner, and further including arranging a conditioning wheel over the pad and relative to the center of the polishing table.
5. (original) A method for chemical-mechanical polishing, according to claim 4, wherein arranging the conditioning wheel comprises thinning the center of the pad.
6. (original) A method for chemical-mechanical polishing, according to claim 1, wherein the wafer is being polished in a center-slow manner, and further including arranging a conditioning wheel over the pad and relative to the center of the polishing table.

7. (original) A method for chemical-mechanical polishing, according to claim 6, wherein arranging the conditioning wheel comprises thinning the edge of the pad.

8. (original) A method for chemical-mechanical polishing, according to claim 1, wherein conditioning the pad comprises altering the thickness of the pad in at least one location.

9. (original) A method for chemical-mechanical polishing, according to claim 8, wherein altering the thickness of the pad comprises thinning the pad in at least one location where the pad is thick relative to the rest of the pad.

10. (previously presented) A method for chemical-mechanical polishing, according to claim 8, wherein altering the thickness of the pad comprises applying increased pressure to a portion of the pad with a conditioning wheel.

11. (previously presented) An arrangement for chemical-mechanical polishing a wafer, the arrangement comprising:

- means for polishing a wafer;

- means for holding a wafer face-down on the means for polishing;

- means for determining whether the wafer is polishing in a center-offset manner; and

- means, responsive to the determination means, for conditioning the polishing means and positioning the wafer misaligned with respect to the polishing means.

12. (previously presented) An arrangement for chemical-mechanical polishing, the arrangement comprising:

- a polishing pad arranged to rotate;

- a wafer carrier arranged to carry a wafer, rotate, and hold the wafer face-down on the polishing pad;

- a detection arrangement adapted to detect whether the wafer is polishing in a center-offset manner; and

a conditioning device adapted to condition the pad, both the conditioning device being arranged, and the wafer carrier being misaligned, relative to the polishing pad as a function of the wafer having been polished in a center-offset manner.

13. (canceled)

14. (original) An arrangement for chemical-mechanical polishing, according to claim 12, further comprising a supply arranged to supply conditioning material to the polishing pad.

15. (original) An arrangement for chemical-mechanical polishing, according to claim 14, wherein the conditioning material is supplied responsive to the detection arrangement.

16. (original) An arrangement for chemical-mechanical polishing, according to claim 15, wherein the conditioning material comprises water.

17. (currently amended) A ~~method~~system for chemical-mechanical polishing a wafer, using a CMP apparatus having a polishing table including a polishing pad and a wafer carrier adapted to carry a wafer relative to the center of the polishing table, the method comprising:

means for using the polishing pad, polishing the wafer at a position relative to the center;

means for determining that the wafer is being polished in a center-offset manner;

means for compensating for the wafer being polished in a center-offset manner by conditioning the pad as a function of the wafer being polished in the center-offset manner, and positioning the wafer carrier misaligned with respect to the pad.

18. (previously presented) A method for chemical-mechanical polishing a wafer, according to claim 1, wherein positioning the wafer carrier misaligned with respect to the pad includes positioning the wafer carrier offset relative to a center of the pad.

19. (previously presented) An arrangement for chemical-mechanical polishing a wafer, according to claim 12, wherein the wafer carrier is offset relative to a center of the pad.